



# CAT661

## High Frequency 100mA CMOS Charge Pump, Inverter/Doubler

### FEATURES

- Converts  $V_+$  to  $V_-$  or  $V_+$  to  $2V_+$
- Low output resistance,  $10\Omega$  max.
- High power efficiency
- Selectable charge pump frequency
  - 25kHz or 135kHz
  - Optimize capacitor size
- Low quiescent current
- Pin-compatible to MAX660, LTC660
  - Higher frequency operation
- Available in 8-pin SOIC, DIP and 0.8mm thin 8-pad TDFN packages
  - Lead-free, halogen-free package option

### APPLICATIONS

- Negative voltage generator
- Voltage doubler
- Voltage splitter
- Low EMI power source
- GaAs FET biasing
- Lithium battery power supply
- Instrumentation
- LCD contrast bias
- Cellular phones, pagers

### DESCRIPTION

The CAT661 is a charge-pump voltage converter. It will invert a 1.5V to 5.5V input to a -1.5V to -5.5V output. Only two external capacitors are needed. With a guaranteed 100mA output current capability, the CAT661 can replace a switching regulator and its inductor. Lower EMI is achieved due to the absence of an inductor.

In addition, the CAT661 can double a voltage supplied from a battery or power supply. Inputs from 2.5V to 5.5V will yield a doubled, 5V to 11V output.

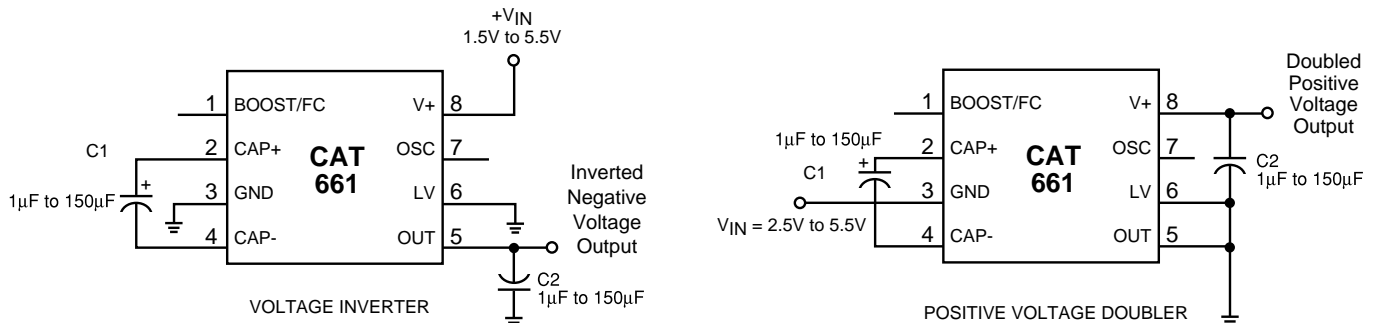
A Frequency Control pin (BOOST/FC) is provided to select either a high (typically 135kHz) or low (25kHz) internal oscillator frequency, thus allowing quiescent current vs. capacitor size trade-offs to be made. The 135kHz frequency is selected when the FC pin is

connected to  $V_+$ . The operating frequency can also be adjusted with an external capacitor at the OSC pin or by driving OSC with an external clock.

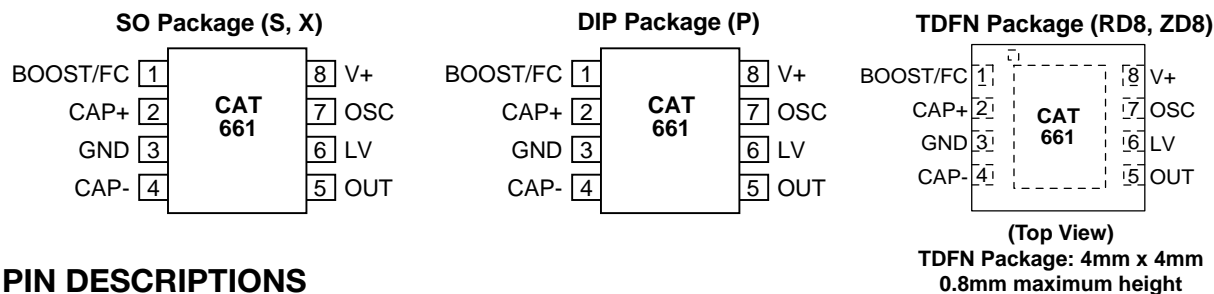
Both 8-pin DIP and SO packages are available in the industrial temperature range. The TDFN package has a 4x4mm footprint and features a 0.8mm maximum height. Compared to the 8-pin SO the TDFN package footprint is nearly 50% less. For die availability, contact Catalyst Semiconductor marketing.

The CAT661 can replace the MAX660 and the LTC®660 in applications where higher oscillator frequency and smaller capacitors are needed. In addition, the CAT661 is pin compatible with the 7660/1044, offering an easy upgrade for applications with 100mA loads.

### TYPICAL APPLICATION



## PIN CONFIGURATION



## PIN DESCRIPTIONS

Pin Number	Name	Circuit Configuration	
		Inverter	Doubler
1	Boost/FC	Frequency Control for the internal oscillator. With an external oscillator BOOST/FC has no effect.	
		<b>Boost/FC</b>	<b>Oscillator Frequency</b>
		Open	25kHz typical, 10kHz minimum
		V+	135kHz typical, 80kHz minimum
2	CAP+	Charge Pump Capacitor. Positive terminal.	Same as inverter.
3	GND	Power Supply Ground.	Power supply. Positive voltage input.
4	CAP-	Charge pump capacitor. Negative terminal.	Same as inverter.
5	OUT	Output for negative voltage.	Power supply ground.
6	LV	Low-Voltage selection pin. When the input voltage is less than 3V, connect LV to GND. For input voltages above 3V, LV may be connected to GND or left open. If OSC is driven externally, connect LV to GND.	LV must be tied to OUT for all input voltages.
7	OSC	Oscillator control input. An external capacitor can be connected to lower the oscillator frequency. An external oscillator can drive OSC and set the chip operating frequency. The charge-pump frequency is one-half the frequency at OSC.	Same as inverter. Do not overdrive OSC in doubling mode. Standard logic levels will not be suitable. See the applications section for additional information.
8	V+	Power supply. Positive voltage input.	Positive voltage output.

## ORDERING INFORMATION

Part Number	Package	Temperature Range
CAT661EPA	8 lead Plastic DIP	-40°C to 85°C
CAT661ESA	8-lead SO	-40°C to 85°C
CAT661ESA-TE13	8-lead SO, Tape & Reel	-40°C to 85°C
CAT661EXA	8-lead SO (Lead-free, Halogen-free)	-40°C to 85°C
CAT661EXA-TE13	8-lead SO (Lead-free, Halogen-free)	-40°C to 85°C
CAT661ERD8	8-pad TDFN	-40°C to 85°C
CAT661EZD8	8-pad TDFN (Lead-free, Halogen-free)	-40°C to 85°C

## ABSOLUTE MAXIMUM RATINGS

V+ to GND ..... 6V

Input Voltage (Pins 1, 6 and 7) .. -0.3V to (V+ + 0.3V)

BOOST/FC and OSC Input Voltage ..... The least negative of (Out - 0.3V) or (V+ - 6V) to (V+ + 0.3V)

Output Short-circuit Duration to GND ..... 1 sec.

(OUT may be shorted to GND for 1 sec without damage but shorting OUT to V+ should be avoided.)

Continuous Power Dissipation (T<sub>A</sub> = 70°C)

Plastic DIP ..... 730mW

SO ..... 500mW

TDFN ..... 1W

Storage Temperature ..... -65°C to 160°C

Lead Soldering Temperature (10 sec) ..... 300°C

Note: T<sub>A</sub> = Ambient Temperature

These are stress ratings only and functional operation is not implied. Exposure to absolute maximum ratings for prolonged time periods may affect device reliability. All voltages are with respect to ground.

### Operating Ambient Temperature Ranges

CAT661E ..... -40°C to 85°C

## ELECTRICAL CHARACTERISTICS

V+ = 5V, C1 = C2 = 150μF, Boost/FC = Open, C<sub>OSC</sub> = 0pF, and Test Circuit is Figure 1 unless otherwise noted. Temperature is T<sub>A</sub> = T<sub>AMIN</sub> to T<sub>AMAX</sub> unless otherwise noted.

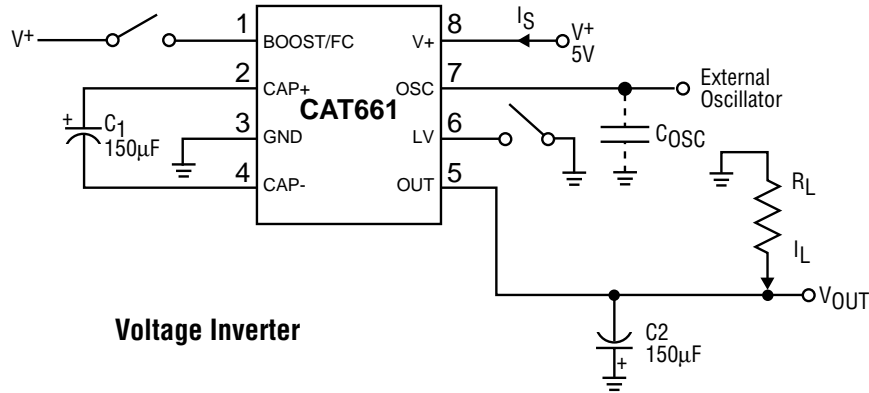
Parameter	Symbol	Conditions	Min.	Typ	Max.	Units
Supply Voltage	VS	Inverter: LV = Open. R <sub>L</sub> = 1kΩ	3.0		5.5	V
		Inverter: LV = GND. R <sub>L</sub> = 1kΩ	1.5		5.5	
		Doubler: LV = OUT. R <sub>L</sub> = 1kΩ	2.5		5.5	
Supply Current	IS	BOOST/FC = open, LV = Open			0.5	mA
		BOOST/FC = V+ , LV = Open		1	3	
Output Current	IOUT	OUT is more negative than -4V	100			mA
Output Resistance	RO	C1 = C2 = 10μF, BOOST/FC = V+ (C1, C2 ESR ≤ 0.5Ω)			15	Ω
		C1 = C2 = 150μF (Note 2)		6.5	10	
Oscillator Frequency (Note 3)	FOSC	BOOST/FC = Open	10	25		kHz
		BOOST/FC = V+	80	135		
OSC Input Current	IOSC	BOOST/FC = Open BOOST/FC = V+		±1 ±5		μA
Power Efficiency	PE	R <sub>L</sub> = 1kΩ connected between V+ and OUT, T <sub>A</sub> = 25°C (Doubler)	96	98		%
		R <sub>L</sub> = 500Ω connected between GND and OUT, T <sub>A</sub> = 25°C (Inverter)	92	96		
		I <sub>L</sub> = 100mA to GND, T <sub>A</sub> = 25°C (Inverter)		88		
Voltage Conversion Efficiency	VEFF	No load, T <sub>A</sub> = 25°C	99	99.9		%

1. In Figure 1, test circuit electrolytic capacitors C1 and C2 are 150μF and have 0.2Ω maximum ESR. Higher ESR levels may reduce efficiency and output voltage.

2. The output resistance is a combination of the internal switch resistance and the external capacitor ESR. For maximum voltage and efficiency keep external capacitor ESR under 0.2Ω.

3. FOsc is tested with C<sub>OSC</sub> = 100pF to minimize test fixture loading. The test is correlated back to C<sub>OSC</sub>=0pF to simulate the capacitance at OSC when the device is inserted into a test socket without an external C<sub>OSC</sub>.

Figure 1. Test Circuit

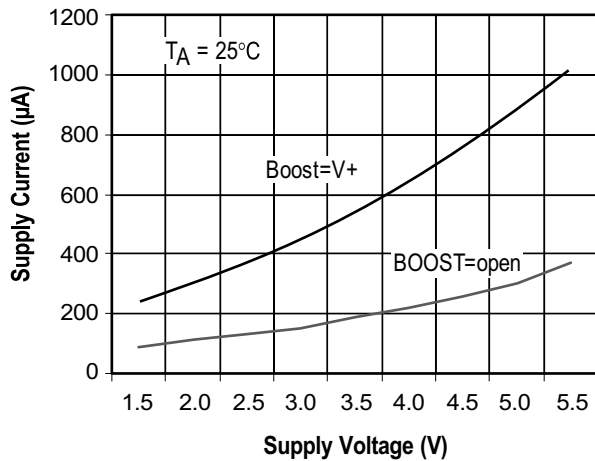


Voltage Inverter

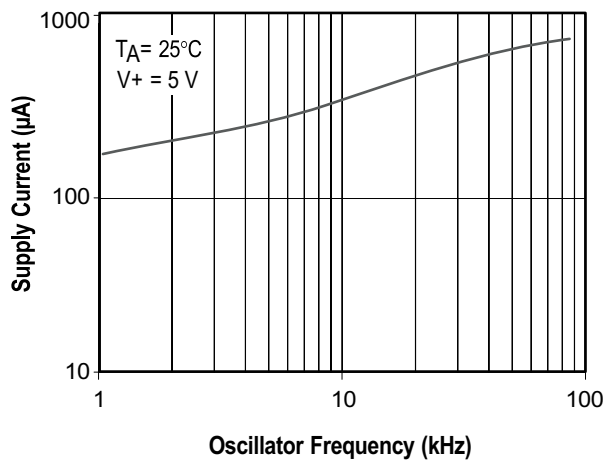
**TYPICAL OPERATING CHARACTERISTICS**

Typical characteristic curves are generated using the circuit in Figure 1. Inverter test conditions are: V+ 5V, LV = GND, BOOST/FC = Open and  $T_A = 25^\circ\text{C}$  unless otherwise indicated. Note that the charge-pump frequency is one-half the oscillator frequency.

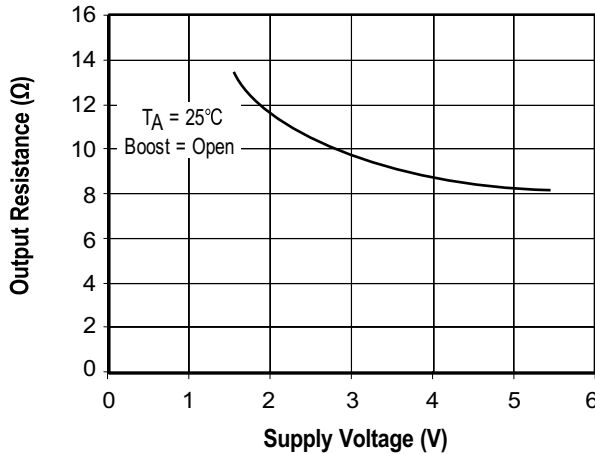
**Supply Current vs. Supply Voltage**



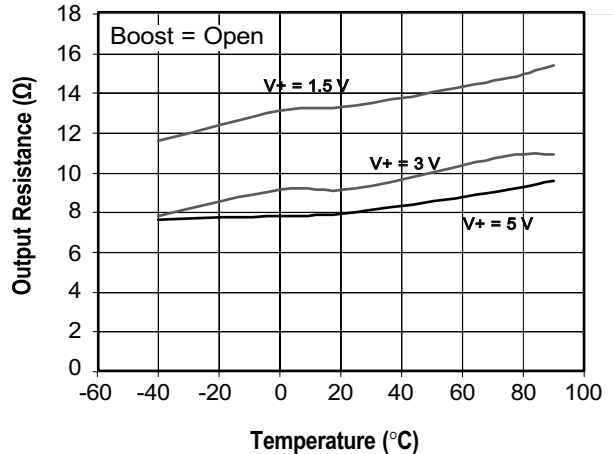
**Supply Current vs. Oscillator Frequency**



**Output Resistance vs. Supply Voltage**

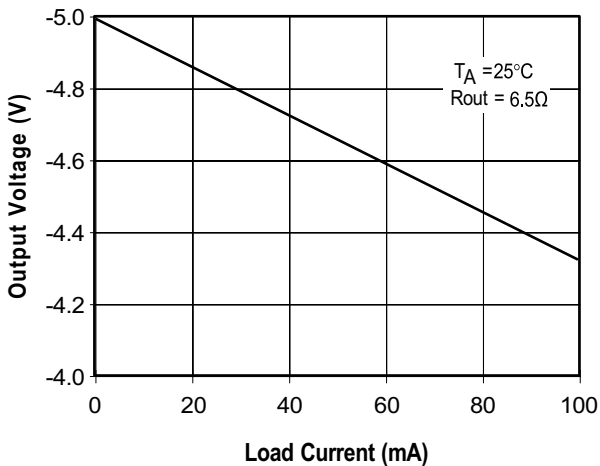


**Output Resistance vs. Temperature**

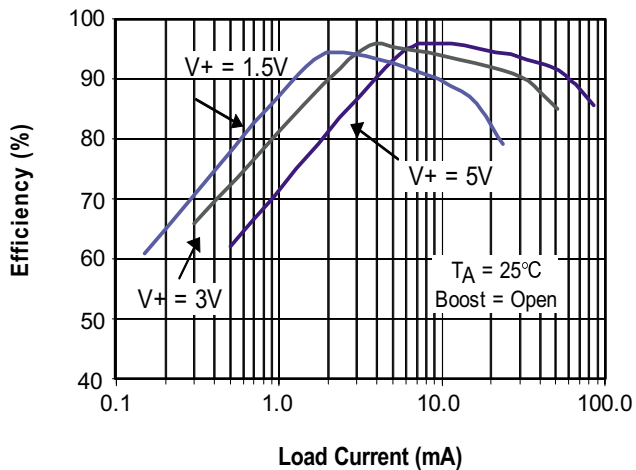


**TYPICAL OPERATING CHARACTERISTICS**

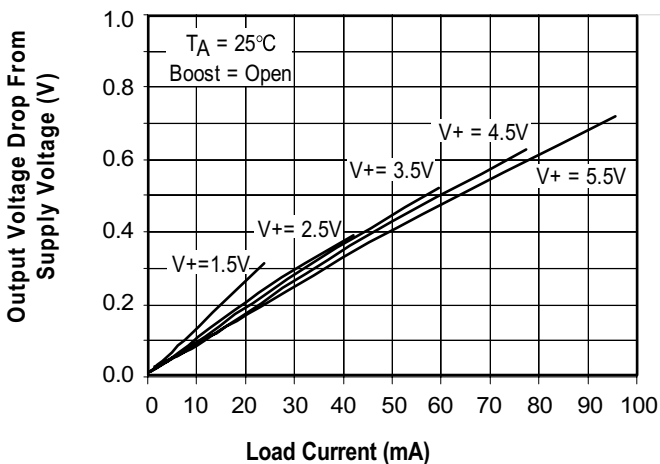
**Output Voltage vs. Load Current, V+=5V**



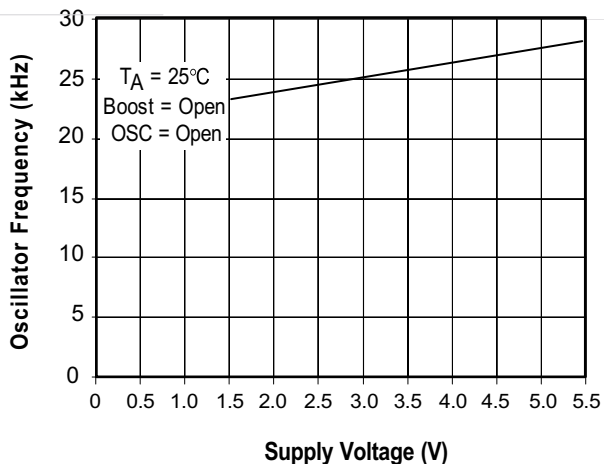
**Efficiency vs. Load Current**



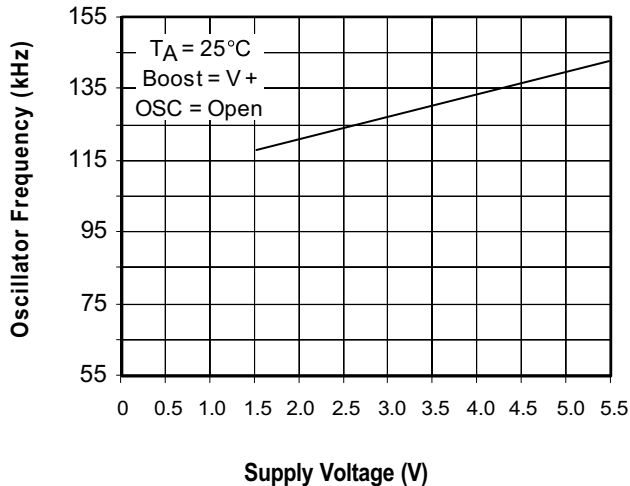
**Output Voltage Drop From Supply Voltage vs. Load Current**



**Oscillator Frequency vs. Supply Voltage**



**Oscillator Frequency vs. Supply Voltage**



**APPLICATION INFORMATION**

**Circuit Description and Operating Theory**

The CAT661 switches capacitors to invert or double an input voltage.

Figure 2 shows a simple switch capacitor circuit. In position 1 capacitor C1 is charged to voltage V1. The total charge on C1 is Q1 = C1V1. When the switch moves to position 2, the input capacitor C1 is discharged to voltage V2. After discharge, the charge on C1 is Q2 = C1V2.

The charge transferred is:

$$\Delta Q = Q1 - Q2 = C1 \times (V1 - V2)$$

If the switch is cycled "F" times per second, the current (charge transfer per unit time) is:

$$I = F \times \Delta Q = F \times C1 (V1 - V2)$$

Rearranging in terms of impedance:

$$I = \frac{(V1-V2)}{(1/FC1)} = \frac{V1-V2}{REQ}$$

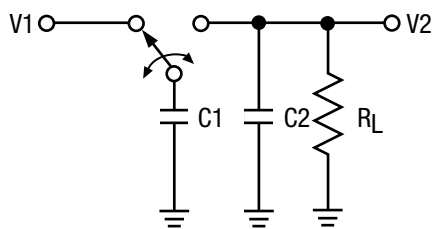
The 1/FC1 term can be modeled as an equivalent impedance REQ. A simple equivalent circuit is shown in figure 3. This circuit does not include the switch resistance nor does it include output voltage ripple. It does allow one to understand the switch-capacitor topology and make prudent engineering tradeoffs.

For example, power conversion efficiency is set by the output impedance, which consists of REQ and switch resistance. As switching frequency is decreased, REQ, the 1/FC1 term, will dominate the output impedance, causing higher voltage losses and decreased efficiency. As the frequency is increased quiescent current increases. At high frequency this current becomes significant and the power efficiency degrades.

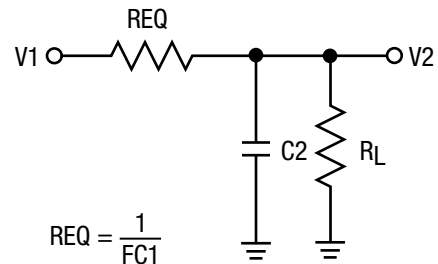
The oscillator is designed to operate where voltage losses are a minimum. With external 150µF capacitors, the internal switch resistances and the Equivalent Series Resistance (ESR) of the external capacitors determine the effective output impedance.

A block diagram of the CAT661 is shown in figure 4.

**Figure 2. Switched-Capacitor Building Block**



**Figure 3. Switched-Capacitor Equivalent Circuit**



### OSCILLATOR FREQUENCY CONTROL

The switching frequency can be raised, lowered or driven from an external source. Figure 5 shows a functional diagram of the oscillator circuit.

The CAT661 oscillator has four control modes:

BOOST/FC Pin Connection	OSC Pin Connection	Nominal Oscillator Frequency
Open	Open	25kHz
BOOST/FC= V+	Open	135kHz
Open or BOOST/FC= V+	External Capacitor	—
Open	External Clock	Frequency of external clock

If BOOST/FC and OSC are left floating (Open), the nominal oscillator frequency is 25kHz. The pump frequency is one-half the oscillator frequency.

By connecting the BOOST/FC pin to V+, the charge and discharge currents are increased, and the frequency is increased by approximately 6 times. Increasing the frequency will decrease the output impedance and ripple currents. This can be an advantage at high load currents. Increasing the frequency raises quiescent current but allows smaller capacitance values for C1 and C2.

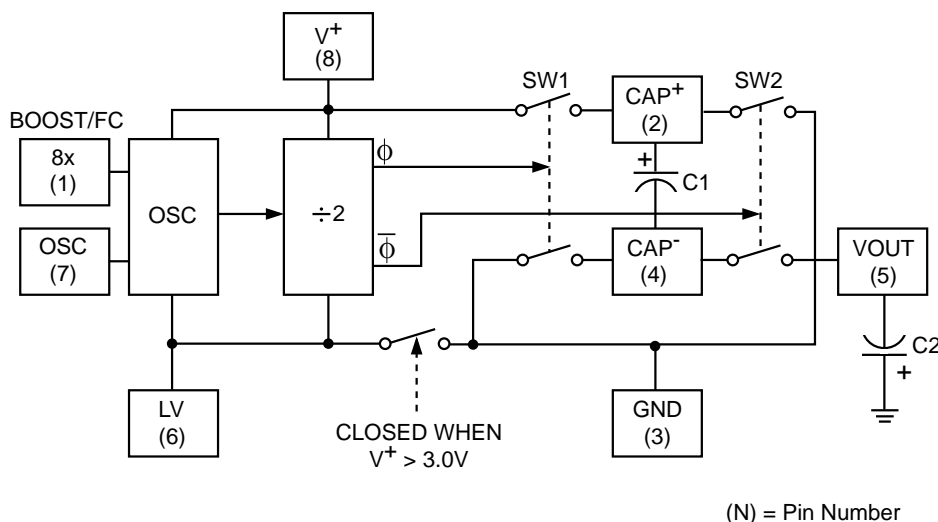
If pin 7, OSC, is loaded with an external capacitor the frequency is lowered. By using the BOOST/FC pin and

an external capacitor at OSC, the operating frequency can be set.

Note that the frequency appearing at CAP+ or CAP- is one-half that of the oscillator.

Driving the CAT661 from an external frequency source can be easily achieved by driving Pin 7 and leaving the BOOST pin open, as shown in figure 6. The output current from Pin 7 is small, typically 1µA to 8µA, so a CMOS can drive the OSC pin. For 5V applications, a TTL logic gate can be used if an external 100kΩ pull-up resistor is used as shown in figure 6.

Figure 4. CAT661 Block Diagram



**CAPACITOR SELECTION**

Low ESR capacitors are necessary to minimize voltage losses, especially at high load currents. The exact values of C1 and C2 are not critical but low ESR capacitors are necessary.

The ESR of capacitor C1, the pump capacitor, can have a pronounced effect on the output. C1 currents are approximately twice the output current and losses occur on both the charge and discharge cycle. The ESR effects are thus multiplied by four. A 0.5Ω ESR for C1 will have the same effect as a 2Ω increase in CAT661 output impedance.

Output voltage ripple is determined by the value of C2 and the load current. C2 is charged and discharged at a current roughly equal to the load current. The internal switching frequency is one-half the oscillator frequency.

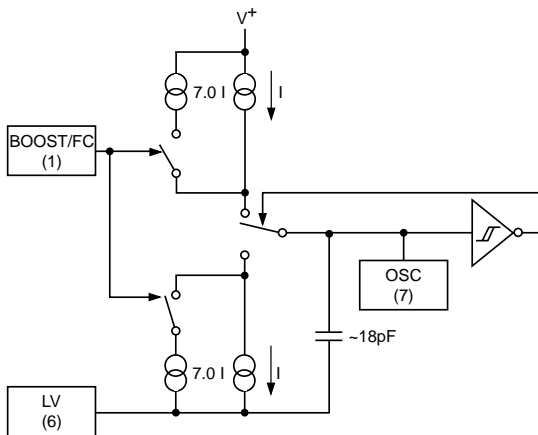
$$VRIPPLE = I_{OUT}/(F_{OSC} \times C2) + I_{OUT} \times ESR_{C2}$$

For example, with a 25kHz oscillator frequency (12.5kHz switching frequency), a 150μF C2 capacitor with an ESR of 0.2Ω and a 100mA load peak-to-peak the ripple voltage is 45mV.

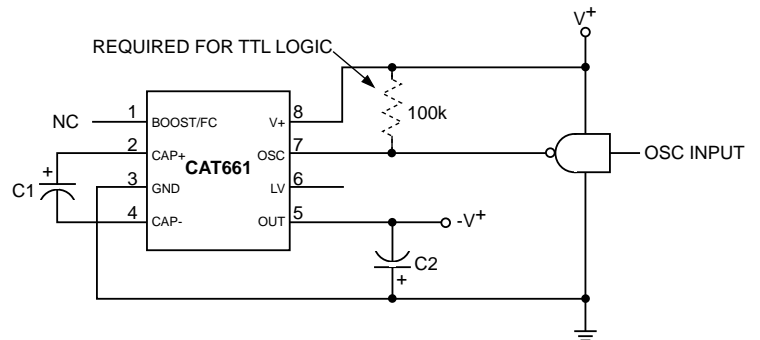
**VRIPPLE vs. FOSC**

VRIPPLE (mV)	IOUT (mA)	FOSC (kHz)	C2 (μF)	C2 ESR (Ω)
45	100	25	150	0.2
25	100	135	150	0.2

**Figure 5. Oscillator**



**Figure 6. External Clocking**





## CAPACITOR SUPPLIERS

The following manufacturers supply low-ESR capacitors:

Manufacturer	Capacitor Type	Phone	WEB	Email	Comments
AVX/Kyocera	TPS/TPS3	843-448-9411	www.avxcorp.com	avx@avxcorp.com	Tantalum
Vishay/Sprague	595	402-563-6866	www.vishay.com	—	Aluminum
Sanyo	MV-AX, UGX	619-661-6835	www.sanyo.com	Svcsales@sanyo.com	Aluminum
Nichicon	F55	847-843-7500	www.nichicon-us.com	—	Tantalum
	HC/HD				Aluminum

Capacitor manufacturers continually introduce new series and offer different package styles. It is recommended

that before a design is finalized capacitor manufacturers should be surveyed for their latest product offerings.

## CONTROLLING LOSS IN CAT661 APPLICATIONS

There are three primary sources of voltage loss:

1. Output resistance  
 $V_{LOSS\Omega} = I_{LOAD} \times R_{OUT}$ , where  $R_{OUT}$  is the CAT661 output resistance and  $I_{LOAD}$  is the load current.
2. Charge pump (C1) capacitor ESR:  
 $V_{LOSSC1} \approx 4 \times ESR_{C1} \times I_{LOAD}$ , where  $ESRC1$  is the ESR of capacitor C1.
3. Output or reservoir (C2) capacitor ESR:  
 $V_{LOSSC2} = ESR_{C2} \times I_{LOAD}$ , where  $ESRC2$  is the ESR of capacitor C2.

Increasing the value of C2 and/or decreasing its ESR will reduce noise and ripple.

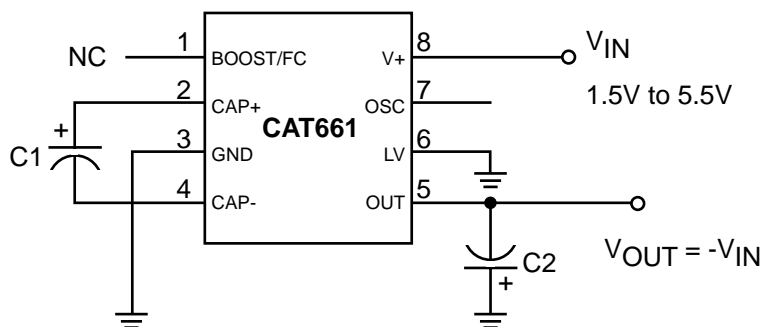
The effective output impedance of a CAT661 circuit is approximately:

$$R_{circuit} \approx R_{out\ 661} + (4 \times ESR_{C1}) + ESR_{C2}$$

## VOLTAGE INVERSION POSITIVE-TO-NEGATIVE

The CAT661 easily provides a negative supply voltage from a positive supply in the system. Figure 8 shows a typical circuit. The LV pin may be left floating for positive input voltages at or above 3.3V.

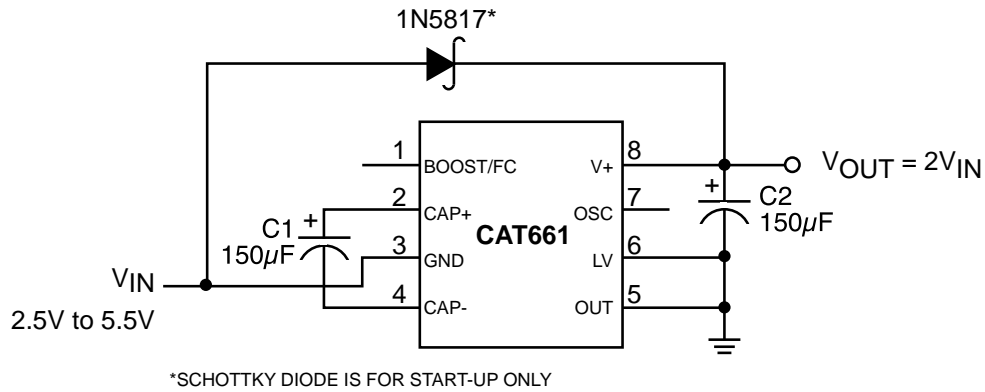
**Figure 8: Voltage Inverter**



**TYPICAL APPLICATIONS**

**POSITIVE VOLTAGE DOUBLER**

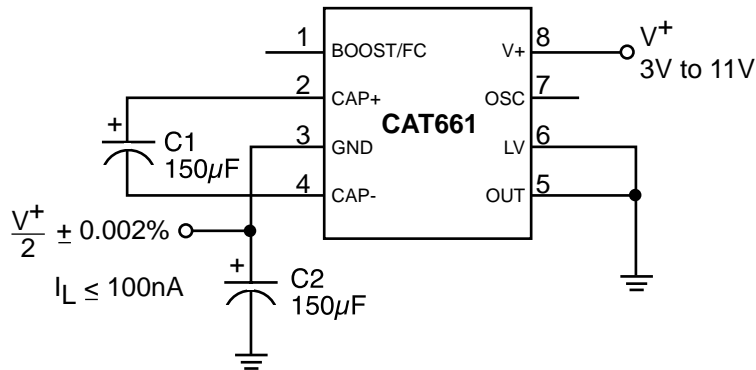
The voltage doubler circuit shown in figure 9 gives  $V_{OUT} = 2 \times V_{IN}$  for input voltages from 2.5V to 5.5V.



**Figure 9: Voltage Doubler**

**PRECISION VOLTAGE DIVIDER**

A precision voltage divider is shown in figure 10. With load currents under 100nA, the voltage at pin 2 will be within 0.002% of  $V^+/2$ .



**Figure 10: Precision Voltage Divider (Load  $\leq 100\text{nA}$ )**

## BATTERY VOLTAGE SPLITTER

Positive and negative voltages that track each other can be obtained from a battery. Figure 11 shows how a 9V battery can provide symmetrical positive and negative voltages equal to one-half the battery voltage.

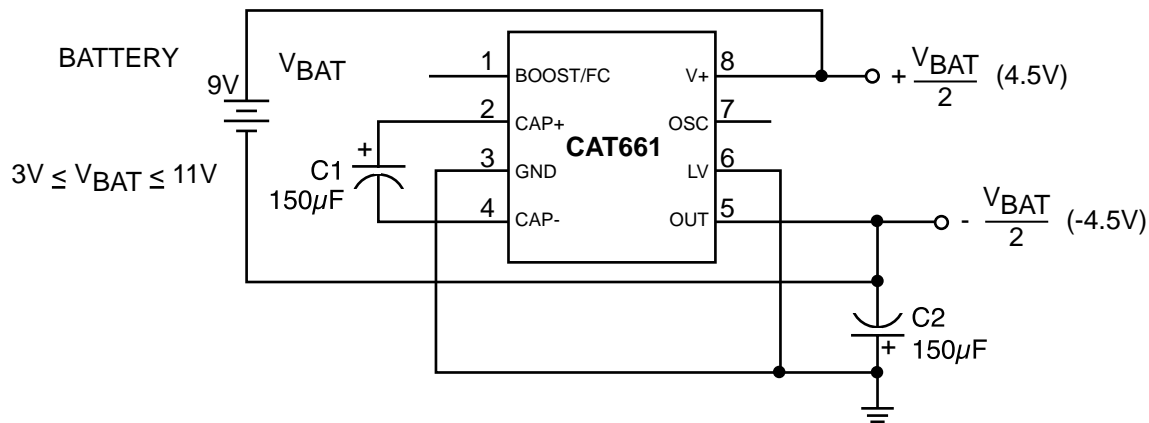


Figure 11: Battery Splitter

## CASCADE OPERATION FOR HIGHER NEGATIVE VOLTAGES

The CAT661 can be cascaded as shown in figure 12 to generate more negative voltage levels. The output resistance is approximately the sum of the individual CAT661 output resistance.

$V_{OUT} = -N \times V_{IN}$ , where N represents the number of cascaded devices.

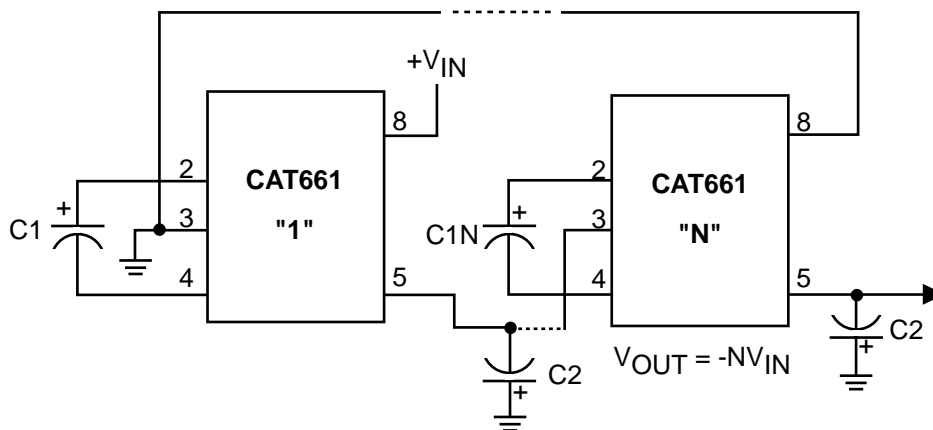
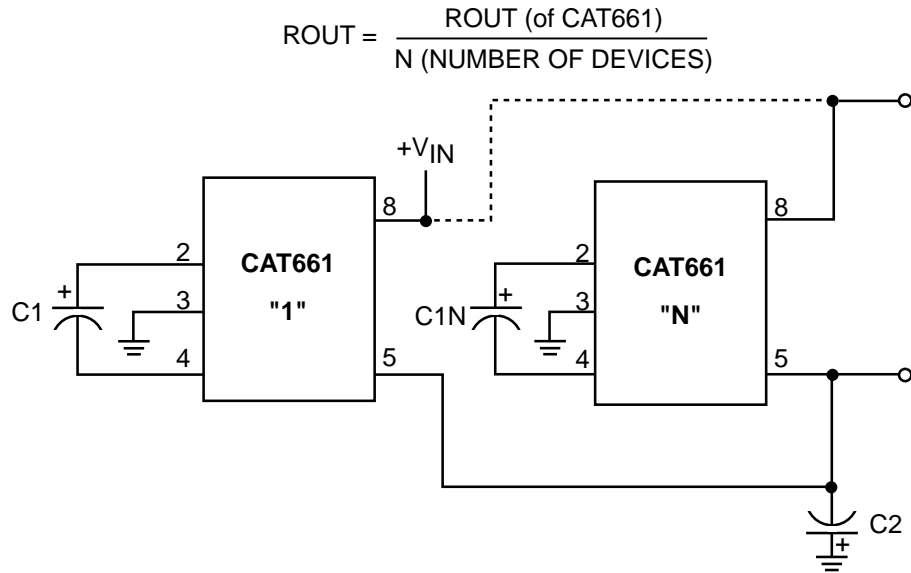


Figure 12: Cascading to Increase Output Voltage

**PARALLEL OPERATION**

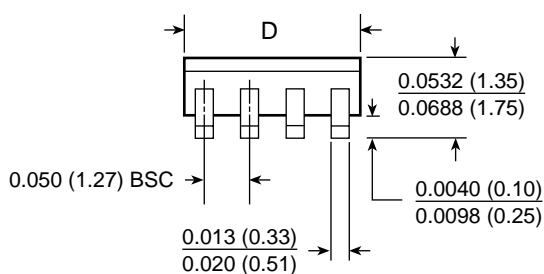
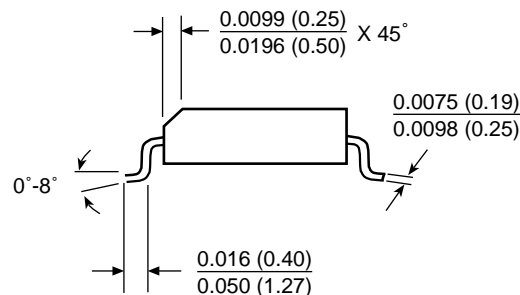
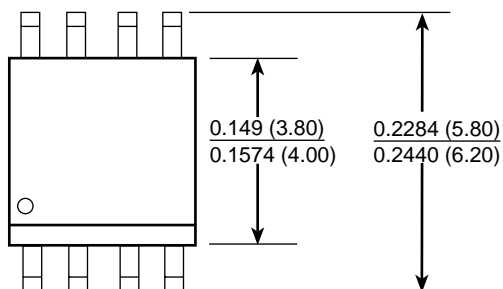
Paralleling CAT661 devices will lower output resistance. As shown in figure 13, each device requires its own pump capacitor, C2, but the output reservoir capacitor is shared with all devices. The value of C2 should be increased by a factor of N, where N is the number of devices.



**Figure 13: Reduce Output Resistance by Paralleling Devices**

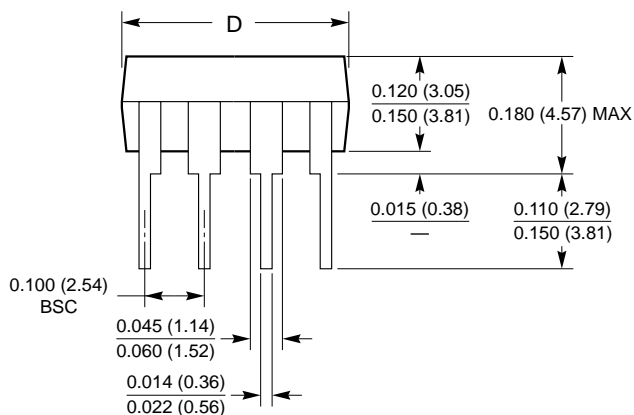
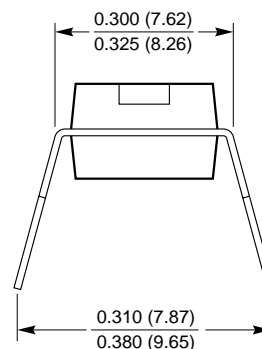
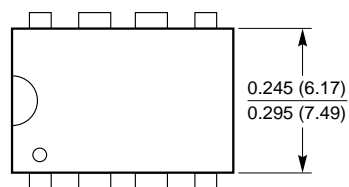
**PACKAGE MECHANICAL DRAWINGS**

**8-LEAD 150 WIDE SOIC (S, X)**



Dimension D		
Pkg	Min	Max
8L	0.1890(4.80)	0.1968(5.00)

**8-LEAD 300 MIL WIDE PLASTIC DIP (P)**

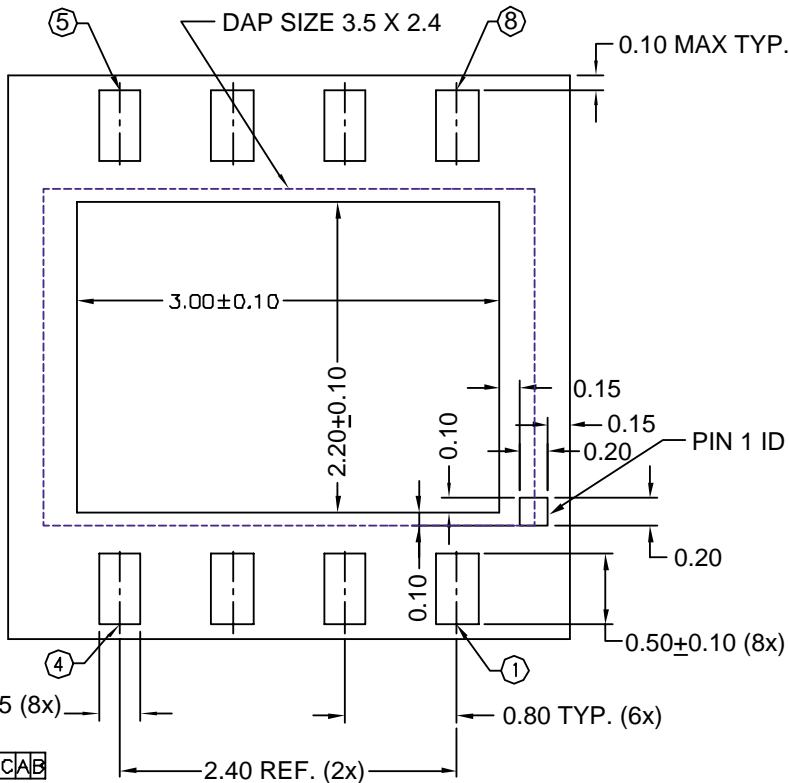
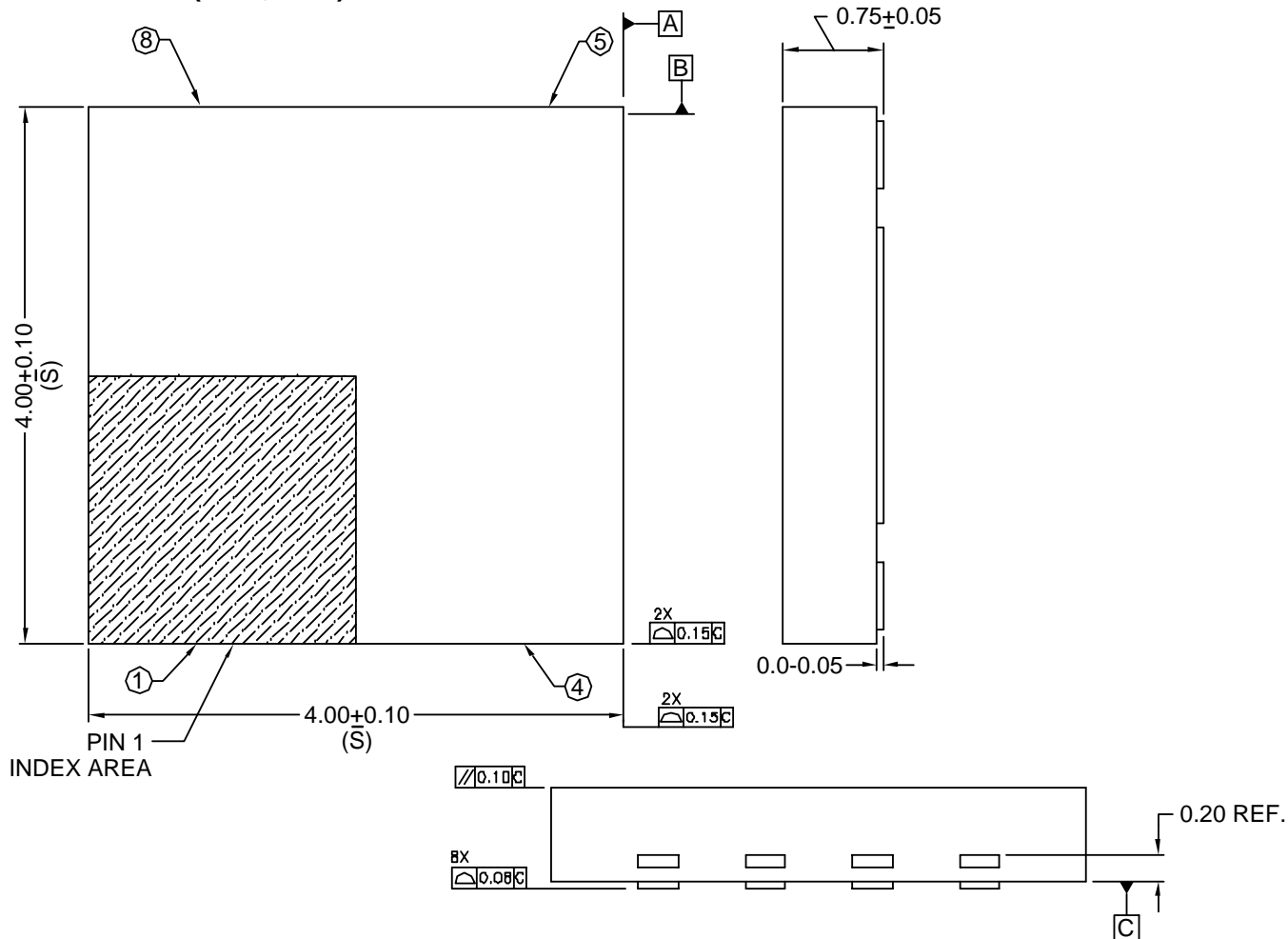


Dimension D		
Pkg	Min	Max
8L	0.355 (9.02)	0.400 (10.16)

**Notes:**

1. Complies with JEDEC Publication 95 MS001 dimensions; however, some of the dimensions may be more stringent.
2. All linear dimensions are in inches and parenthetically in millimeters.

8-PAD TDFN (RD8, ZD8)



NOTE:

1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
2. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS. COPLANARITY SHALL NOT EXCEED 0.08mm.
3. WARPAGE SHALL NOT EXCEED 0.10mm.
4. PACKAGE LENGTH/PACKAGE WIDTH ARE CONSIDERED AS SPECIAL CHARACTERISTIC. (S)

**REVISION HISTORY**

<b>Date</b>	<b>Rev.</b>	<b>Reason</b>
10/15/03	G	Updated Description - eliminated Commercial temperature range

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